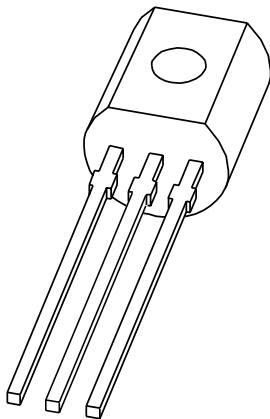


DATA SHEET



BC635; BC637; BC639 NPN medium power transistors

Product specification
Supersedes data of 1997 Mar 12

1999 Apr 23

NPN medium power transistors

BC635; BC637; BC639

FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V).

APPLICATIONS

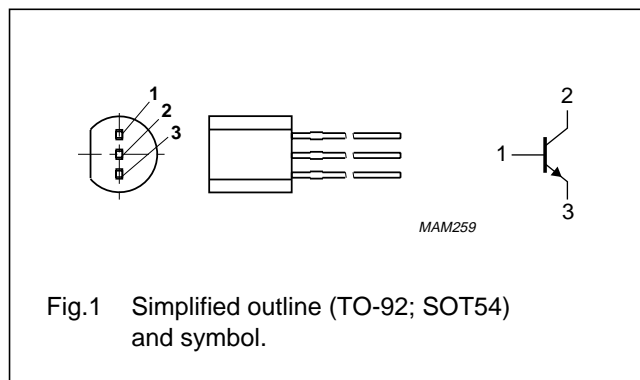
- Driver stages of audio/video amplifiers.

DESCRIPTION

NPN transistor in a TO-92; SOT54 plastic package.
PNP complements: BC636, BC638 and BC640.

PINNING

PIN	DESCRIPTION
1	base
2	collector
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage BC635 BC637 BC639	open emitter	— — —	45 60 100	V V V
V_{CEO}	collector-emitter voltage BC635 BC637 BC639	open base	— — —	45 60 80	V V V
V_{EBO}	emitter-base voltage	open collector	—	5	V
I_C	collector current (DC)		—	1	A
I_{CM}	peak collector current		—	1.5	A
I_{BM}	peak base current		—	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	—	0.83	W
T_{stg}	storage temperature		−65	+150	$^{\circ}\text{C}$
T_j	junction temperature		—	150	$^{\circ}\text{C}$
T_{amb}	operating ambient temperature		−65	+150	$^{\circ}\text{C}$

NPN medium power transistors

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	150	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	100	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 2\text{ V}$; see Fig.2			
		$I_C = 5\text{ mA}$	40	–	
		$I_C = 150\text{ mA}$	63	250	
		$I_C = 500\text{ mA}$	25	–	
	DC current gain	$I_C = 150\text{ mA}; V_{CE} = 2\text{ V}$; see Fig.2			
	BC639-10		63	160	
	BC635-16; BC637-16; BC639-16		100	250	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	500	mV
V_{BE}	base-emitter voltage	$I_C = 500\text{ mA}; V_{CE} = 2\text{ V}$	–	1	V
f_T	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	MHz
$\frac{h_{FE1}}{h_{FE2}}$	DC current gain ratio of the complementary pairs	$ I_C = 150\text{ mA}; V_{CE} = 2\text{ V}$	–	1.6	

NPN medium power transistors

BC635; BC637; BC639

